

L Number	Hits	Search Text	DB	Time stamp
-	0	(depolarization or (charge adj reduct?\$\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same (plasma adj flood adj gun)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 11:55
-	237	(depolarization or (charge adj reduct?\$\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:20
-	4068	((depolarization or (charge adj reduct?\$\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma) (wafer adj fabrication)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:21
-	30	((depolarization or (charge adj reduct?\$\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma) and wafer	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:25
-	79	depolarization adj (method or process)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:25
-	90	((charge adj reduct?\$\$5) or depolarization) adj (method or process)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:26
-	0	((charge adj reduct?\$\$5) or depolarization) adj (method or process)) and (expos?\$\$5 with plasma)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:27
-	11	((charge adj reduct?\$\$5) or depolarization) adj (method or process)) and plasma	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 10:27
-	7553	(depolarization or (de adj polarization))	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 12:03
-	6	((depolarization or (de adj polarization))) and (wafer adj fabricat?\$\$5)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 11:58
-	12	((electrostatic adj discharge) or esd) with (wafer adj fabricat?\$\$5)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 12:02
-	0	(polarization adj charge?) with (wafer adj fabricat?\$\$5)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 12:03
-	1	(depolarization or (de adj polarization)) with (wafer adj fabricat?\$\$5)	USPAT; US-PPGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/27 12:05

	0	depolarization with (wafer near2 pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:08
	37	semiconductor adj fabrication adj tool?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:08
	0	(semiconductor adj fabrication adj tool?) with (discharge near2 electrostatic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:10
	0	(semiconductor adj fabrication adj tool?) with ((discharge near2 electrostatic) or esd or (electrostatic adj discharge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:10
	0	(semiconductor adj fabrication adj tool?) same ((discharge near2 electrostatic) or esd or (electrostatic adj discharge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:11
	207	(ion adj implantation) same ((electrostatic adj charge) or esd or (electrostatic adj discharge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:12
	41	((ion adj implantation) same ((electrostatic adj charge) or esd or (electrostatic adj discharge))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:12
	1	(wafer near2 pad) with (depolarization or (de adj polarization) or (electrostatic adj discharge) or esd or (charge near2 (reduct?\$\$ or neutralization)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:45
	4	(("5089710") or ("5399871")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 13:25
	0	("(insulating near2 pad) with plasma").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:36
	14	(insulating near2 pad) with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:38
	118741	(H01L021/3065 or H01L021/205 or H01L021/31 or H01L021/68).ipc.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:39
	23297	((H01L021/3065 or H01L021/205 or H01L021/31 or H01L021/68).ipc.) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:39
	3	((H01L021/3065 or H01L021/205 or H01L021/31 or H01L021/68).ipc.) and plasma) and (insulating near3 pad?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:39